

Trans IGBT Chip N-CH 2500V 156A 735mW 3-Pin(3+Tab) PLUS 247



Manufacturer:	Littelfuse Inc
Package/Case:	TO-247
Product Type:	Thyristors
Lifecycle:	Active

Images are for reference only

[Inquiry](#)

General Description

BiMOSFETs are devices, which have combined strengths of MOSFETs and IGBTs. Non-epitaxial construction and new fabrication processes were used in making BiMOSFETs a great success. These high voltage devices are ideal for parallel operation due to the positive voltage temperature coefficient of both of its saturation voltage, and the forward voltage drop of its intrinsic diode. Furthermore, this “free” intrinsic body diode serves as a protection diode, providing an alternative path for the inductive load current during device turn-off, preventing high Ldi/dt voltage transients from inflicting damage to the device.

Key Features

- High power density
- High frequency operation
- Low conduction losses
- MOS gate turn on for drive simplicity
- 4000V electrical isolation
- Advantages:
- Low gate drive requirements
- Space savings (eliminates multiple series-parallel lower voltage, lower current rated devices)
- Easy to mount

Application

- Switched-mode and resonant-mode power supplies
- Uninterruptible Power Supplies (UPS)
- Laser and X-ray generators
- Capacitor discharge circuits
- High voltage pulser circuits
- High voltage test equipment
- AC switches

Recommended For You

IX4351NE

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